



HiPerFRED

advanced

1200 V  $V_{RRM}$ 

60 A

35 ns

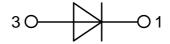
High Performance Fast Recovery Diode Low Loss and Soft Recovery Single Diode

Part number

**DSEP60-12B** 



Backside: cathode



## Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

## **Applications:**

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

## Terms \_Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

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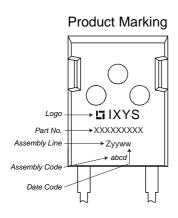
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Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V <sub>RSM</sub>	max. non-repetitive reverse blocki	ng voltage	$T_{VJ} = 25^{\circ}C$			1200	V
V <sub>RRM</sub>	max. repetitive reverse blocking v	oltage	$T_{VJ} = 25^{\circ}C$			1200	V
I <sub>R</sub>	reverse current, drain current	V <sub>R</sub> =1200 V	$T_{VJ} = 25^{\circ}C$			200	μΑ
		$V_R = 1200 \text{ V}$	$T_{VJ} = 150$ °C			1	mΑ
V <sub>F</sub>	forward voltage drop	I <sub>F</sub> = 60 A	$T_{VJ} = 25^{\circ}C$			3.25	V
		$I_F = 120 A$				3.90	V
		I <sub>F</sub> = 60 A	T <sub>VJ</sub> = 150°C			2.20	V
		$I_F = 120 \text{ A}$				2.85	V
I <sub>FAV</sub>	average forward current	T <sub>C</sub> = 110°C	T <sub>vJ</sub> = 175°C			60	Α
		rectangular d = 0.5					1 1 1 1
V <sub>F0</sub>	threshold voltage	an anti-station with	T <sub>VJ</sub> = 175°C			1.10	V
r <sub>F</sub>	slope resistance	ss calculation only				15	mΩ
R <sub>thJC</sub>	thermal resistance junction to case	9				0.45	K/W
R <sub>thCH</sub>	thermal resistance case to heatsir	nk			0.25		K/W
P <sub>tot</sub>	total power dissipation		$T_C = 25^{\circ}C$			330	W
I <sub>FSM</sub>	max. forward surge current	$t = 10 \text{ ms}$ ; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			500	Α
C	junction capacitance	$V_R = 600 \text{V}$ f = 1 MHz	$T_{VJ} = 25^{\circ}C$		30		pF
I <sub>RM</sub>	max. reverse recovery current	\	$T_{VJ} = 25 ^{\circ}\text{C}$		11		Α
		$I_F = 60 \text{ A}; V_R = 600 \text{ V}$	$T_{VJ} = 100 ^{\circ}\text{C}$		17		Α
t <sub>rr</sub>	reverse recovery time	$\begin{cases} I_F = 60 \text{ A; } V_R = 600 \text{ V} \\ -di_F /dt = 200 \text{ A/} \mu \text{s} \end{cases}$	$T_{VJ} = 25 ^{\circ}\text{C}$		65		ns
		l	$T_{VJ} = 100^{\circ}C$		190		ns



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Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I <sub>RMS</sub>	RMS current	per terminal			70	Α
T <sub>VJ</sub>	virtual junction temperature		-55		175	°C
T <sub>op</sub>	operation temperature		-55		150	°C
$T_{stg}$	storage temperature		-55		150	°C
Weight				6		g
M <sub>D</sub>	mounting torque		0.8		1.2	Nm
<b>F</b> <sub>c</sub>	mounting force with clip		20		120	Ν



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEP60-12B	DSEP60-12B	Tube	30	501210

Similar Part	Package	Voltage class
DSEP60-12A	TO-247AD (2)	1200

Equiva	alent Circuits for	Simulation	* on die level	T <sub>VJ</sub> = 175 °C
$I \rightarrow V_0$	)—R <sub>o</sub>	Fast Diode		
V <sub>0 max</sub>	threshold voltage	1.1		V
$R_{0 \text{ max}}$	slope resistance *	12.4		mΩ